2SC3934

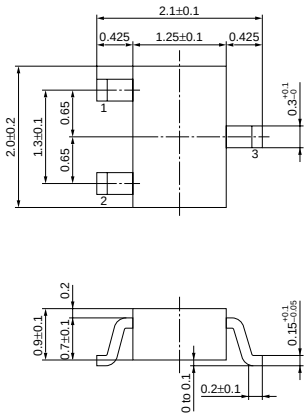
Silicon NPN epitaxial planer type

For high-frequency wide-band low-noise amplification

Features

- High transition frequency f_T.
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Unit: mm



1:Base
2:Emitter EIAJ:SC–70
3:Collector S–Mini Type Package

Marking symbol : 1U

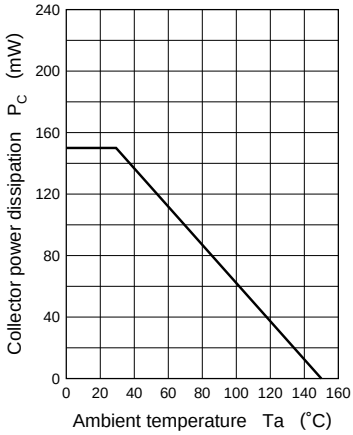
Absolute Maximum Ratings (Ta=25˚C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	12	V
Emitter to base voltage	V_{EBO}	2.5	V
Peak collector current	I_{CP}	50	mA
Collector current	I_C	30	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	˚C
Storage temperature	T_{stg}	–55 ~ +150	˚C

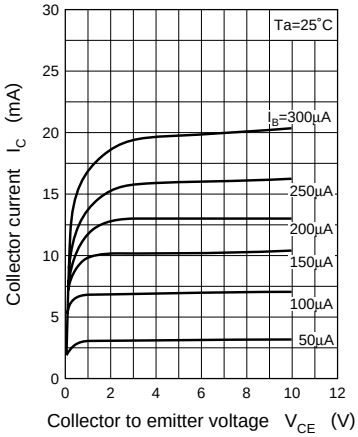
Electrical Characteristics (Ta=25˚C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 10V, I_E = 0			100	µA
Emitter cutoff current	I_{EBO}	V_{EB} = 2V, I_C = 0			1	µA
Forward current transfer ratio	h_{FE}	V_{CE} = 10V, I_C = 10mA	40			
Transition frequency	f_T	V_{CE} = 10V, I_C = 10mA, f = 800MHz		4.5		GHz
Collector output capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz			1.2	pF
Foward transfer gain	$\|S_{21e}\|^2$	V_{CE} = 10V, I_C = 20mA, f = 800MHz	9	12		dB
Maximum unilateral power gain	GUM	V_{CE} = 10V, I_C = 20mA, f = 800MHz	12	14		dB
Noise figure	NF	V_{CE} = 10V, I_C = 5mA, f = 800MHz		1.3	2.5	dB

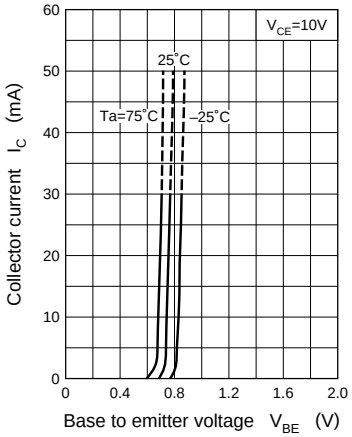
P_C — Ta



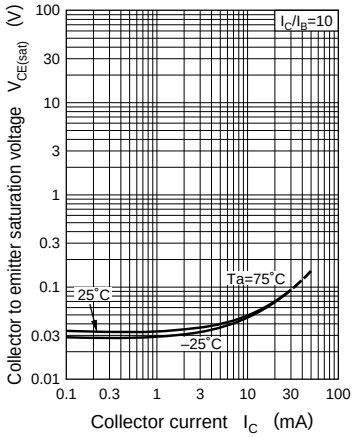
I_C — V_{CE}



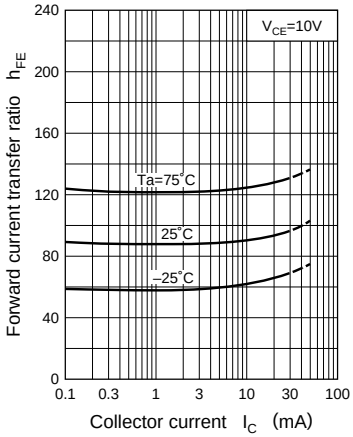
I_C — V_{BE}



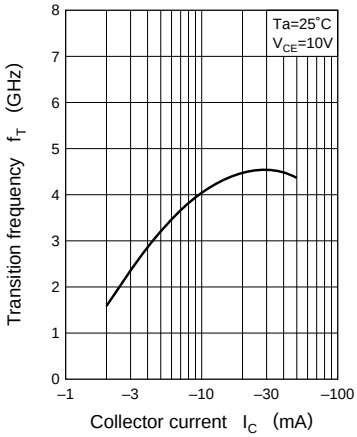
$V_{CE(sat)}$ — I_C



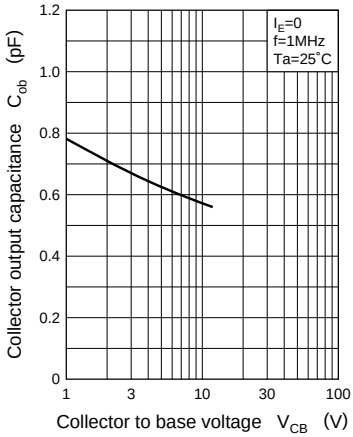
h_{FE} — I_C



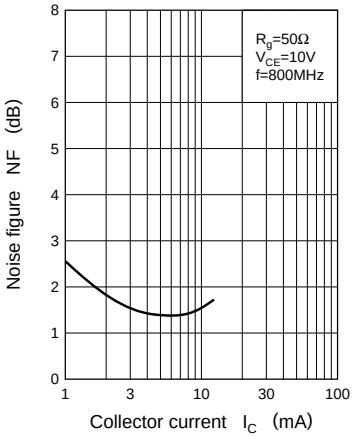
f_T — I_C



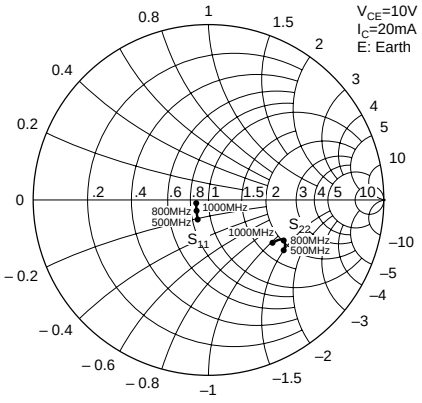
C_{ob} — V_{CB}



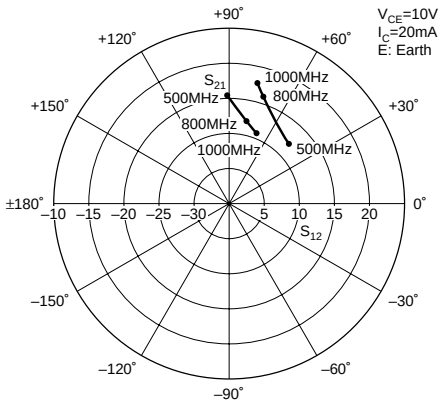
NF — I_C



S_{11}, S_{22}



S_{12}, S_{21}


+90°
+120°
+60°
+150°
+30°
±180°
0°
–150°
–30°
–120°
–60°
–90°
V_{CE}=10V
I_C=20mA
E: Earth
S_{21}
1000MHz
800MHz
500MHz
800MHz
1000MHz
500MHz
–10 –15 –20 –25 –30 5 10 15 20
S_{12}